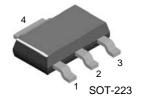


January 2007

BCP69 **PNP General Purpose Amplifier**

- This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.0A.
- Sourced from Process 77.



1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings* Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	-20	V
V _{CBO}	Collector-Base Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-5.0	V
I _C	Collector Current - Continuous	-1.5	Α
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	- 55 ~ + 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics* Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
P_{D}	Total Device Dissipation Derate above 25°C	1.0 8.0	W mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

^{*} Device mounted on FR-4 PCB 36mm × 18mm × 1.5mm; mounting pad for the collector lead min. 6cm²

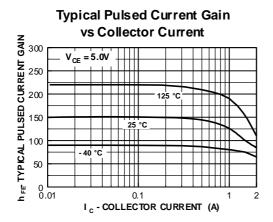
Electrical Characteristics* T_a = 25°C unless otherwise noted

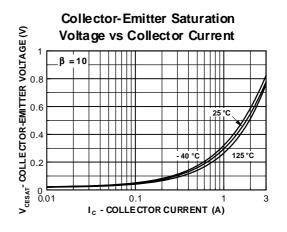
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA, I _B = 0	-20			V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = -1.0 \text{mA}, I_E = 0$	-30			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = -100 \mu A, I_C = 0$	-5.0			V
I _{CBO}	Collector-Base Cutoff Current	$V_{CB} = -25V, I_E = 0$ $V_{CB} = -25V, I_E = 0, T_j = 150^{\circ}C$			-100 -10	nA uA
I _{EBO}	Emitter-Base Cutoff Current	$V_{EB} = -5.0V, I_{C} = 0$			-100	nA
h _{FE}	DC Current Gain	I_{C} = -5mA, V_{CE} = -1.0V I_{C} = -500mA, V_{CE} = -1.0V I_{C} = -1.0A, V_{CE} = -1.0V	50 85 60		375	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1.0A, I _B = -100mA			-0.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -1.0A, V _{CE} = -1.0V			-1.0	V
C _{cb}	Collector-Base Capacitance	$V_{CB} = -10V, I_{E} = 0, f = 1.0MHz$			30	pF
h _{fe}	Small-Signal Current Gain	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V}, f = 20 \text{MHz}$	2.5			

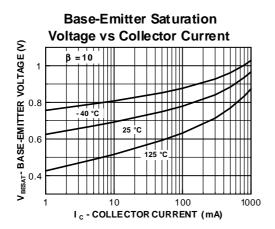
^{*} Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

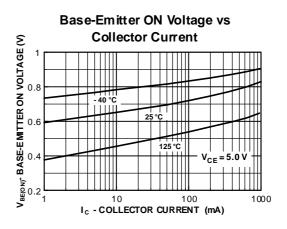
¹⁾ These ratings are based on a maximum junction temperature of 150°C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

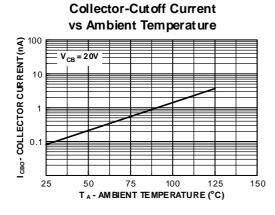
Typical Performance Characteristics

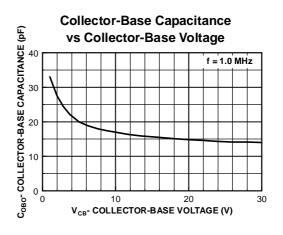




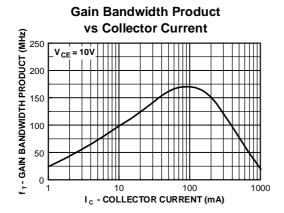


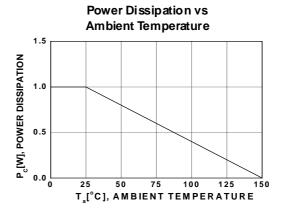






Typical Performance Characteristics

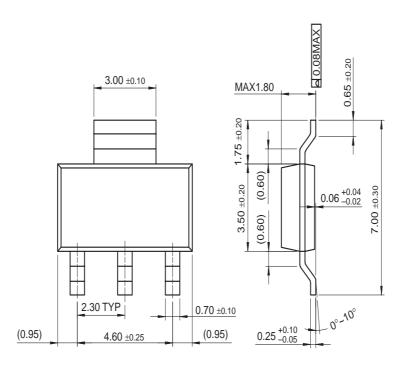


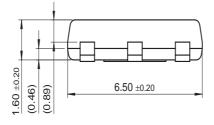


3

Mechanical Dimensions

SOT-223





Dimensions in Millimeters

UniFET™

 VCX^{TM}

Wire™



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The Power Franchise®

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PRODUCT STATUS DEFINITIONS

Definition of Terms

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Rev. 122